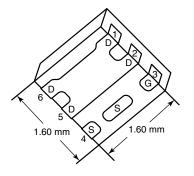


Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY								
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)					
- 20	0.058 at V _{GS} = - 4.5 V	- 9 ^a						
	0.077 at V _{GS} = - 2.5 V	- 9 ^a	7.6 nC					
	0.105 at V _{GS} = - 1.8 V	- 5						

PowerPAK SC-75-6L-Single



FEATURES

- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK® SC-75 Package
 - Small Footprint Area
- Low On-Resistance
- 100 % R_g Tested Typical ESD Performance 2000 V
- Built in ESD Protection with Zener Diode
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

Lot Traceability and Date code

APPLICATIONS

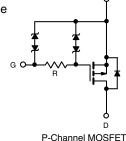
Part # code

- Load Switch for Portable Devices
- Charger Switch for Portable Devices

Marking Code

BLX

• X X X т



Ordering Information: SiB433EDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 20	V		
Gate-Source Voltage		V _{GS}	± 8	v		
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 °C$ $T_{C} = 70 °C$ $T_{A} = 25 °C$ $T_{A} = 70 °C$	I _D	- 9 ^a - 9 ^a - 5.3 ^{b, c} - 4.3 ^{b, c}	A		
Pulsed Drain Current		I _{DM}	- 20			
Continuous Source-Drain Diode Current	T _C = 25 °C T _A = 25 °C	I _S	- 9 ^a - 2 ^{b, c}	-		
Maximum Power Dissipation	$T_{C} = 25 °C$ $T_{C} = 70 °C$ $T_{A} = 25 °C$ $T_{A} = 70 °C$	P _D	13 8.4 2.4 ^{b, c} 1.6 ^{b, c}	w		
Operating Junction and Storage Temperature R	ange	T _J , T _{stg}	- 55 to 150			
Soldering Recommendations (Peak Temperatur	e) ^{d, e}		260			

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit						
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	41	51	°C/W					
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	7.5	9.5	0/11					

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 105 °C/W.

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COMPLIANT HALOGEN FREE

Document Number: 65652 For technical support, please contact: pmostechsupport@vishav.com www.vishav.com S12-0979-Rev. B, 30-Apr-12

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Drain-Source Breakdown Voltage	V_{DS} $V_{GS} = 0 V, I_D = -250 \mu A$		- 20			V		
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I _D = - 250 μA		- 13		mV/°C		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_{\rm D} = -250 \mu \text{A}$		2.5		mv/ C		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	- 0.4		- 1	V		
Gate-Source Leakage	lasa	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$		± 6				
Gale-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 4.5 V$			± 0.5	μA		
	1	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1			
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 15			Α		
		V_{GS} = - 4.5 V, I _D = - 3.7 A		0.047	0.058	Ω		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V_{GS} = - 2.5 V, I _D = - 3.2 A		0.064	0.077			
		V _{GS} = - 1.8 V, I _D = - 1.5 A		0.085	0.105	1		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 3.7 A		12		S		
Dynamic ^b								
•	Qg	V_{DS} = - 10 V, V_{GS} = - 8 V, I_{D} = - 5.3 A		14	21	nC		
Total Gate Charge				7.6	12			
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 5.3 A		0.8				
Gate-Drain Charge	Q _{gd}			3.1				
Gate Resistance	Rg	f = 1 MHz	0.4	2	4	kΩ		
Turn-On Delay Time	t _{d(on)}			0.2	0.3			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 2.3 Ω		1	1.5	-		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 4.3 Å, V_{GEN} = - 4.5 V, R_g = 1 Ω		4	6			
Fall Time				2	3			
Turn-On Delay Time	t _{d(on)}			0.09	0.14	- μs - -		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 2.3 Ω		0.4	0.6			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 4.3 A, V_{GEN} = - 8 V, R_g = 1 Ω		5.2	7.8			
Fall Time	t _f			2.3	3.5			
Drain-Source Body Diode Characterist	ics							
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			- 9	_		
Pulse Diode Forward Current	I _{SM}				- 20	A		
Body Diode Voltage	V _{SD}	I _S = - 4.3 A, V _{GS} = 0 V		- 0.8	- 1.2	V		
Body Diode Reverse Recovery Time	t _{rr}			30	60	ns		
Body Diode Reverse Recovery Charge	Q _{rr}			20	40	nC		
Reverse Recovery Fall Time	t _a	$I_F = -4.3 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^\circ\text{C}$		13				
Reverse Recovery Rise Time	t _b			17		ns		

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

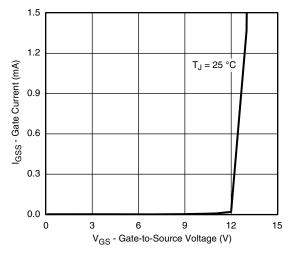
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

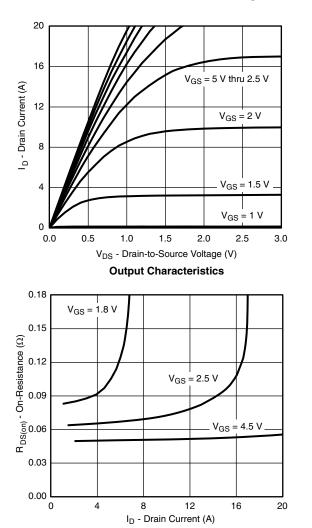


SiB433EDK Vishay Siliconix

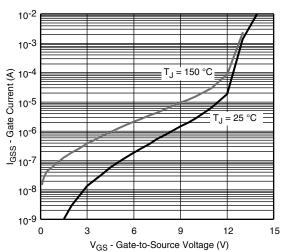
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



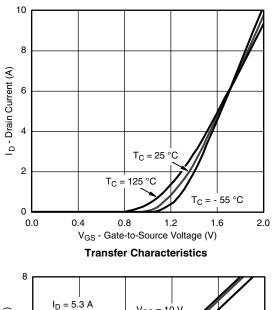


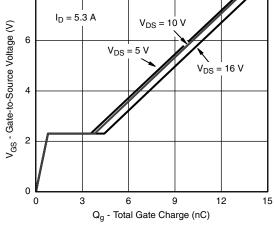


On-Resistance vs. Drain Current



Gate Current vs. Gate-Source Voltage





Gate Charge

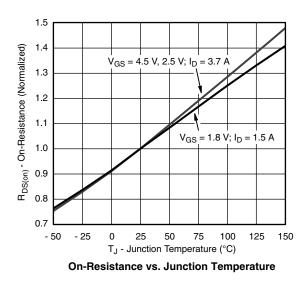
3

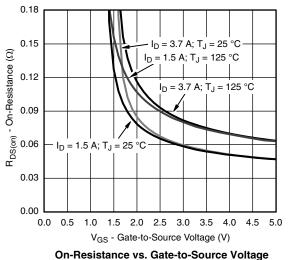
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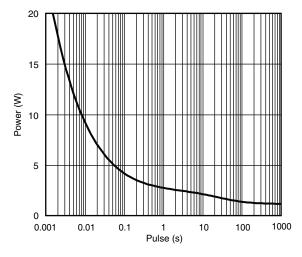


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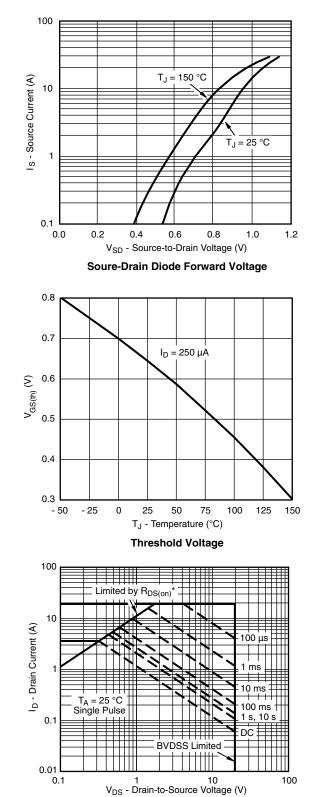
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified Safe Operating Area, Junction-to-Ambient

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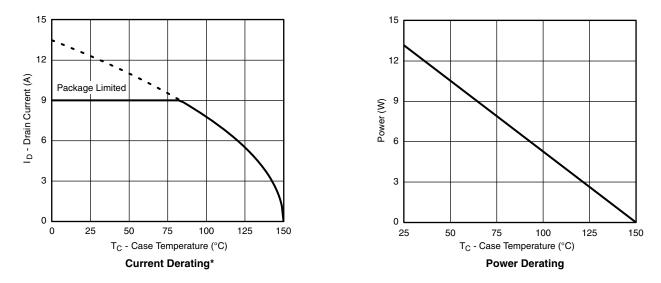
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

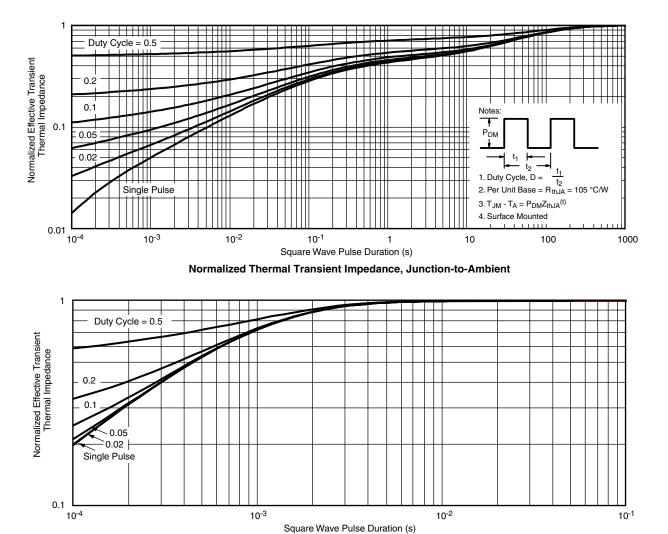


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/ tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65652.

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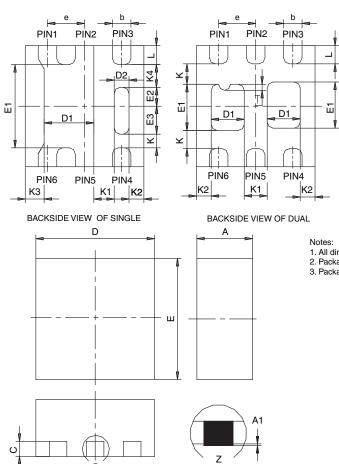
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Package Information

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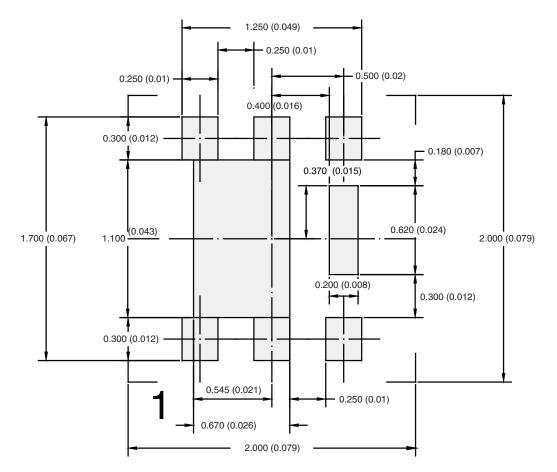
- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

DETAIL Z

	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
е		0.50 BSC			0.020 BSC		0.50 BSC			0.020 BSC		
К		0.180 TYP			0.007 TYP		0.245 TYP		0.010 TYP			
K1		0.275 TYP			0.011 TYP		0.320 TYP			0.013 TYP		
K2	0.200 TYP 0.008 TYP			0.200 BSC 0.008 TY			0.008 TYP					
K3	0.255 TYP 0.010 TYP											
K4	0.300 TYP		0.012 TYP									
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
Т							0.03	0.08	0.13	0.001	0.003	0.005
ECN: C-07431 – Rev. C, 06-Aug-07 DWG: 5935												



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC75-6L Single



Dimensions in mm/(Inches)

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